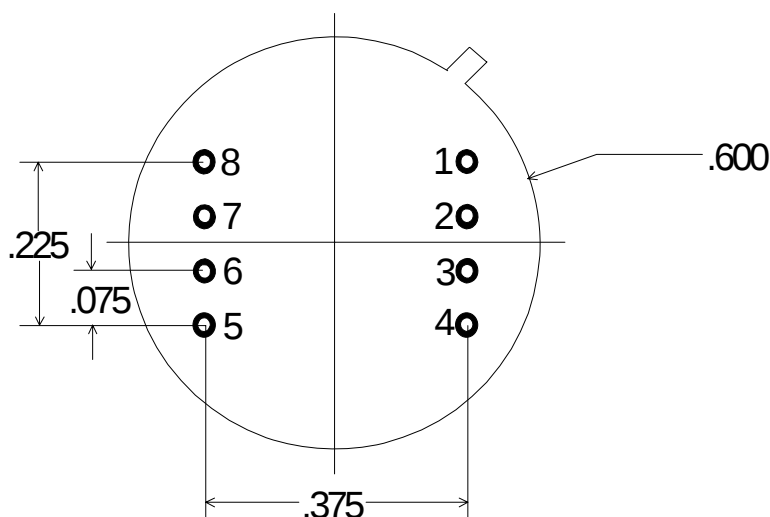
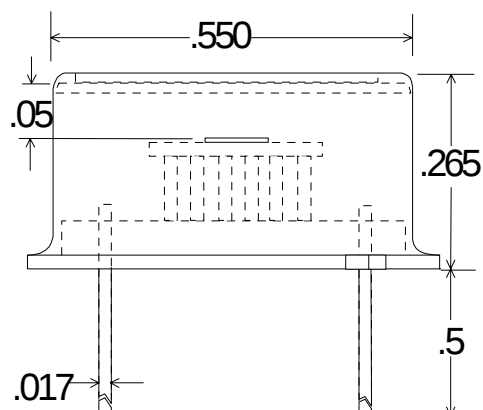




TO - STYLE PHOTODIODE / AMPLIFIER



SILICON - E8 - SERIES

PIN OUT

- 1 = Offset Adj
- 2 = Inv In / Photodiode Cathode
- 3 = N-Inv In / Photodiode Anode
- 4 = -V
- 5 = Gain Select
- 6 = Output
- 7 = +V
- 8 = Offset Adj

Note: Dimensions in Inches

OPERATING INSTRUCTIONS:

This unit is a high performance photodiode/transimpedance amplifier unit. The output voltage is equal to the optical signal power multiplied by the photodiode responsivity in A/W and the feedback resistance in ohms. The unit is DC-coupled and should be shielded from stray or room lights to avoid saturation of the amplifier.

SPECIFICATIONS

Part Number	S-010-E8	S-025-E8	S-050-E8	S-058-E8
Active Area	1mm dia	2.5mm dia	5mm dia	5.8mm x 5.8mm
+ Operating Wavelength	300 - 1000 nm			
Photodiode Shunt Resistance (MΩ)	1000.	250.	100.	100.
Photodiode Shunt Capacitance (pF)	50. typ	250. typ	400. typ	1000. typ
* Output Responsivity @ 850nm, HI/LO (V/W),	$0.55 \times 10^{10} / 10^9$	$0.55 \times 10^9 / 10^8$	$0.55 \times 10^9 / 10^8$	$0.55 \times 10^9 / 10^8$
Bandwidth (Hz)	DC - 100			
NEP (100Hz, 850nm) (W/Hz ^{1/2})	$< 1.0 \times 10^{-14}$	$< 1.2 \times 10^{-14}$	$< 1.5 \times 10^{-14}$	$< 1.2 \times 10^{-14}$
* Note: Other gain values can be specified				